

Domain Manipulation with a light touch: Light assisted poling in ferroelectrics.

**Robert Eason, Sakellaris Mailis, Collin Sones,
Chris Valdivia, Iain Wellington.**

[Optoelectronics Research Centre](#), University of Southampton,
Highfield, SO17 1BJ, UK. E-mail: rwe@orc.soton.ac.uk



**University
of Southampton**



Contents

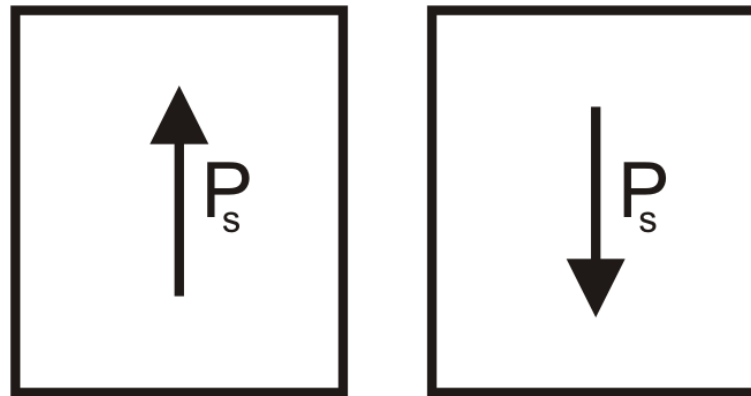
1. Ferroelectric materials and domains
2. Domain manipulation (poling)
3. Light assisted poling (LAP)
4. All optical poling (AOP): **Regular periodic arrays** v. random self-organisation.
5. Latent poling:
6. Mechanisms and conclusions

1. Ferroelectrics (lithium niobate)

- Ferroelectrics properties:
 - Nonlinear (frequency conversion, QPM)
 - Piezoelectric (MEMS, electromechanical)
 - Electro-optic (modulators)
 - Photorefractive (storage, holography)
 - Acousto-optic (modulators)
 - Pyroelectric (detectors)

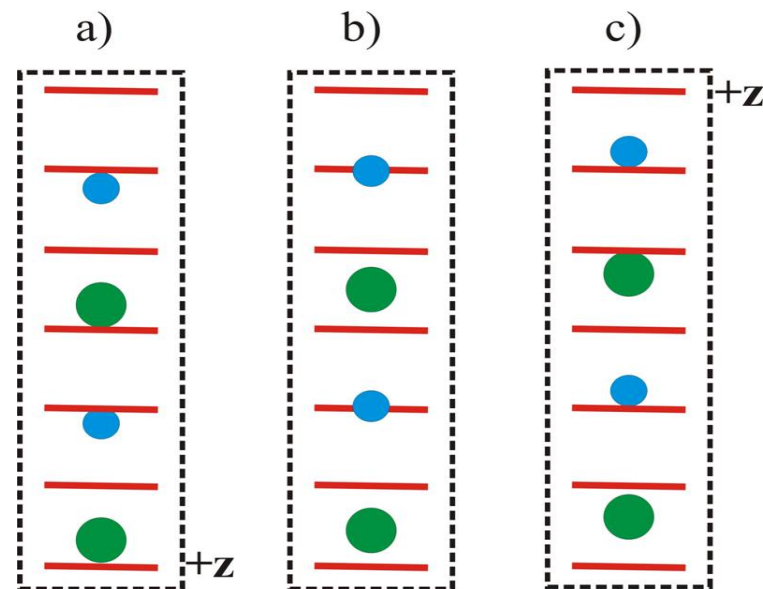
1. Ferroelectric materials and domains

- Ferroelectric crystals possess a spontaneous polarization, P_s
- Two stable “up” and “down” domains
- Second-order nonlinear susceptibility, $\chi^{(2)}$, has sign reversal needed for QPM



1. Ferroelectrics and domains

- Domain structure is important, and *can be engineered*: **Lithium niobate**



● Lithium
● Niobium
— Oxygen

1.Tensor properties

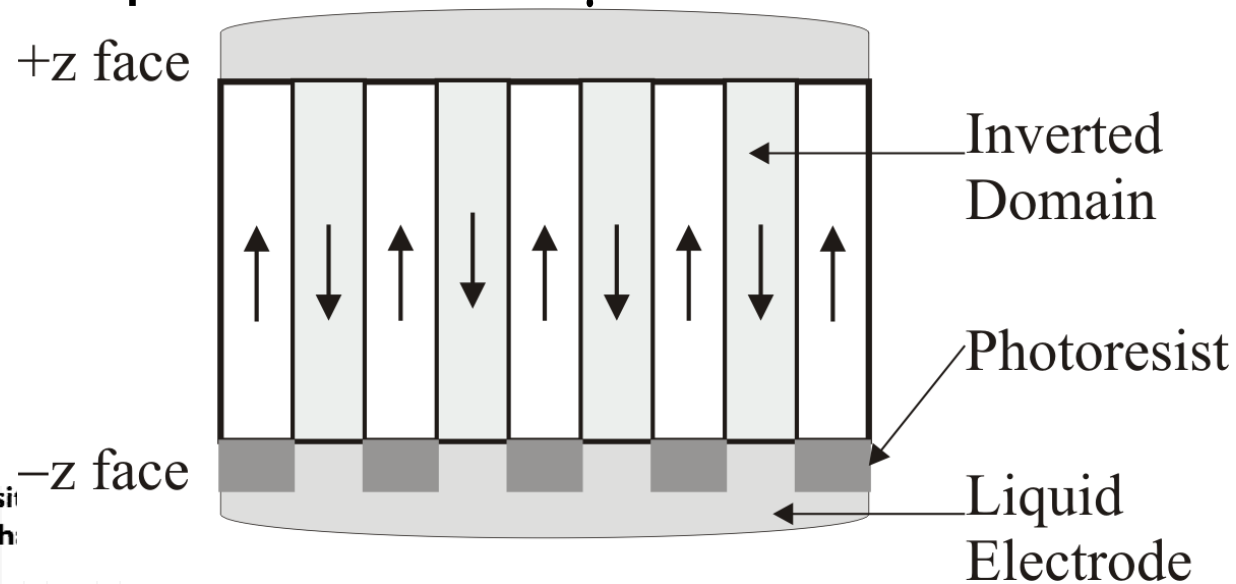
- All properties are governed by domain orientation (+z c.f. -z)
- The **sign** of all coefficients is reversed, hence:
 - QPM devices.
 - Electro-optic switching (induced $\pm \Delta n$)
$$\Delta n = -\frac{1}{2} r E n^3 \quad (+r \text{ or } -r)$$
 - Cancellation of photorefractive..

1. Spatial domain patterning

- Need controllable technique for domain patterning over large areas (cm squared) that is:
 - Easy
 - Fast
 - Can make small sizes ($< 1\mu\text{m}$)
 - Of variable depth (but at least waveguide dimension)

2. E-field Domain Inversion

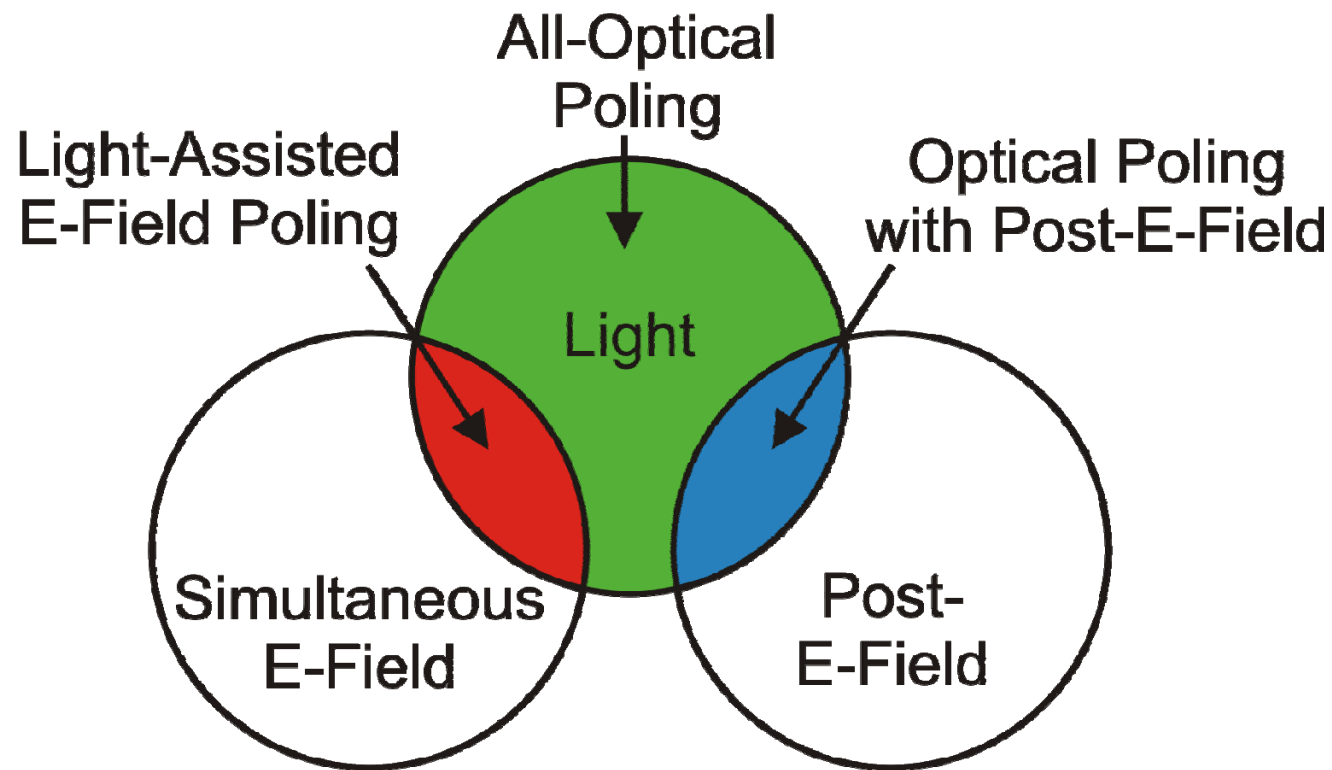
- Domains switched by E-field
 - Coercive field, $E_c \sim 22 \text{ kV mm}^{-1}$
- Form QPM grating: PPLN
- Typical periods: 4-18 μm



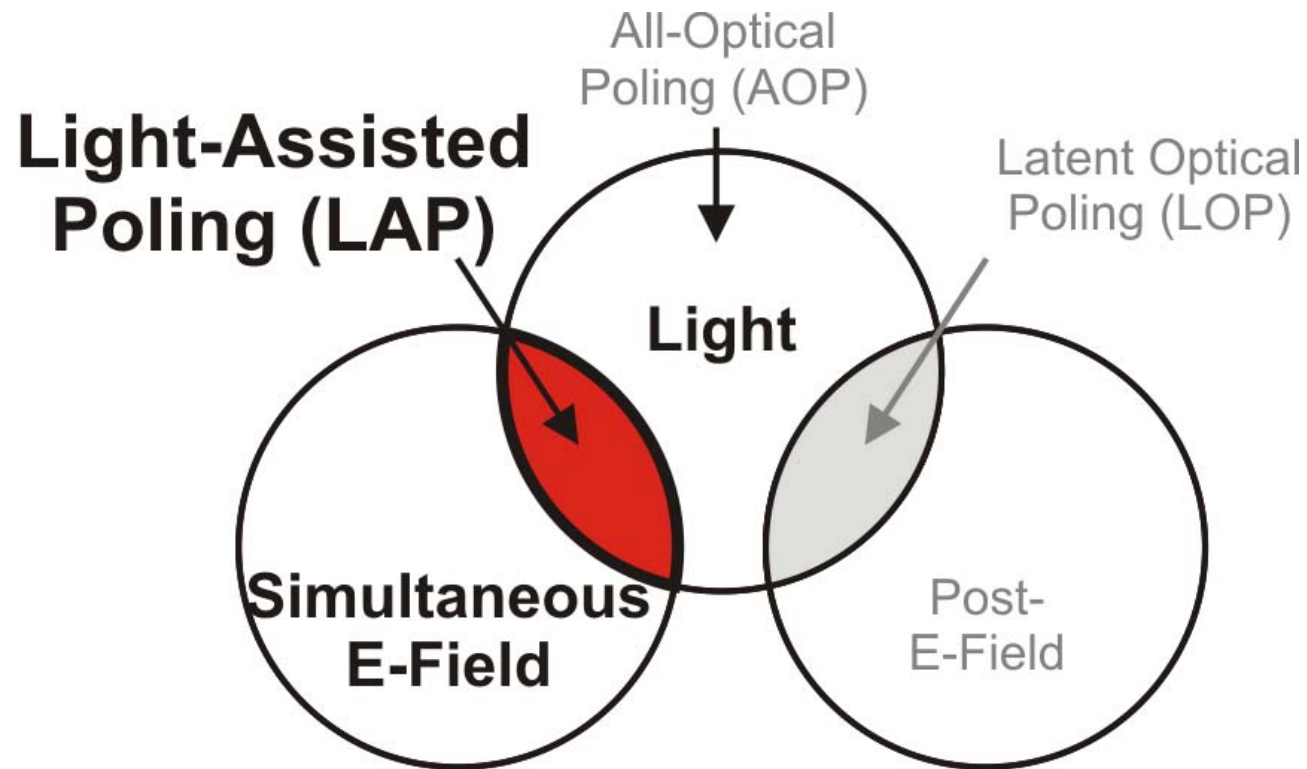
2. Alternative domain inversion techniques

- E-beam irradiation: charging a problem.
- Ion beam, focussed ion beam: expensive.
- AFM: small areas only (100 μ m squared: stitching needed).
- Try using photons?

3. Optical poling techniques

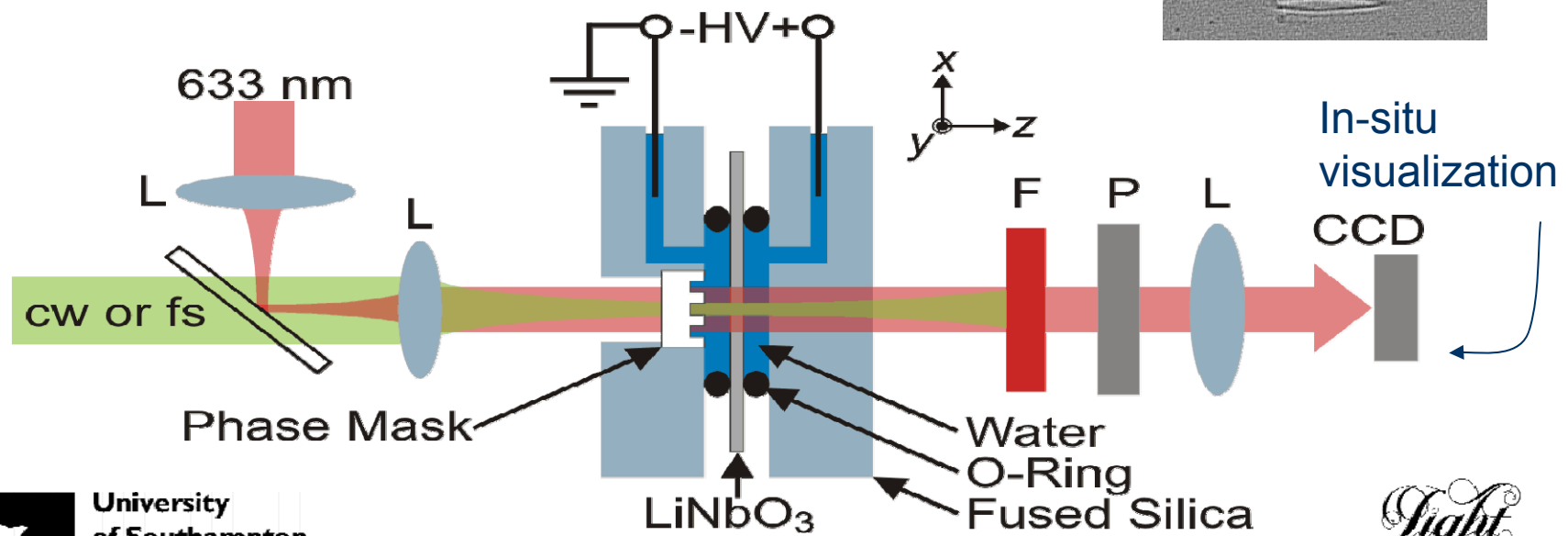


3. Light-assisted poling

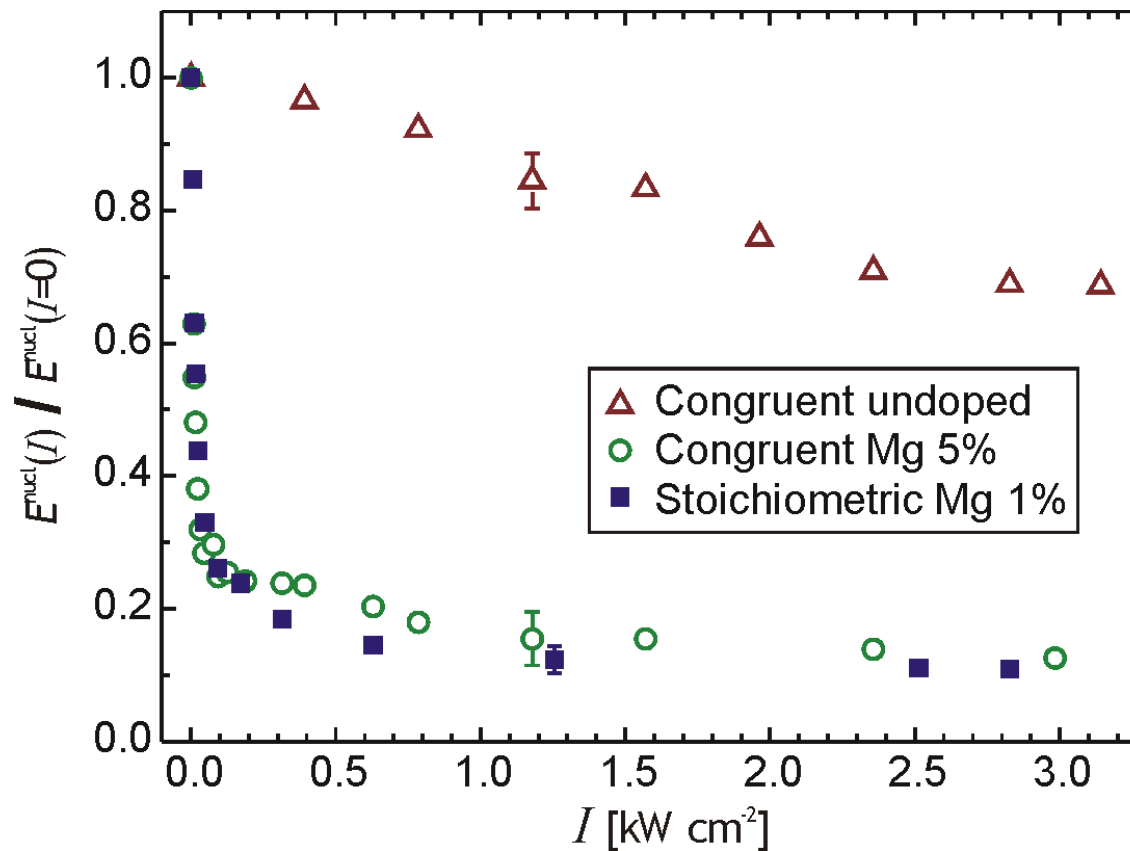


3. Light-Assisted Poling (LAP)

- Simultaneously apply:
 - E-field \rightarrow uniform over crystal
 - Light \rightarrow conveys pattern



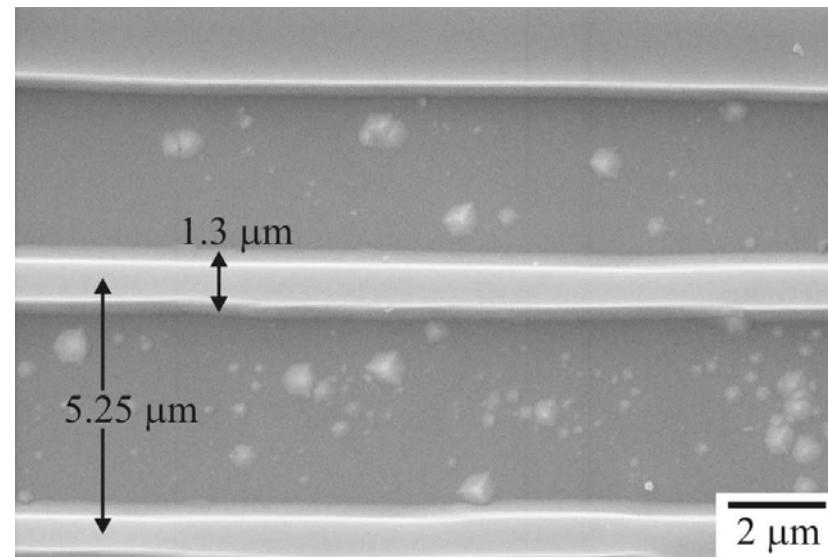
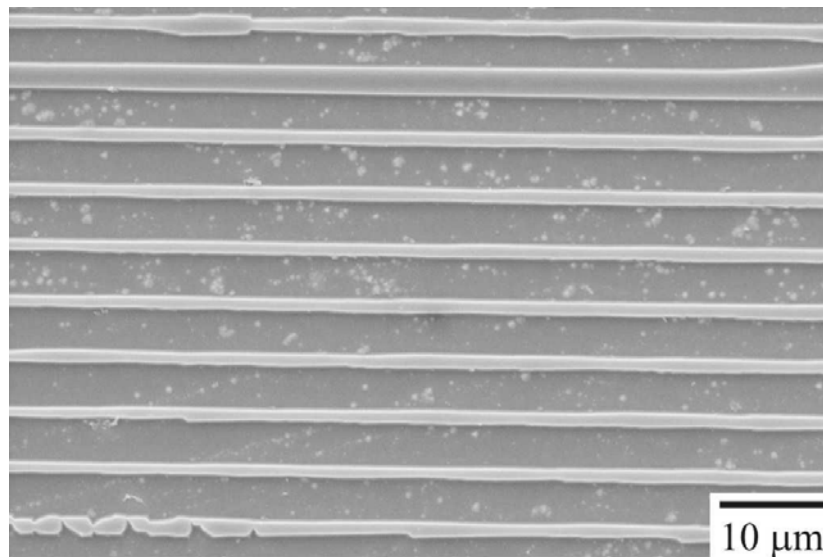
3. Domain inversion (nucleation) c.w



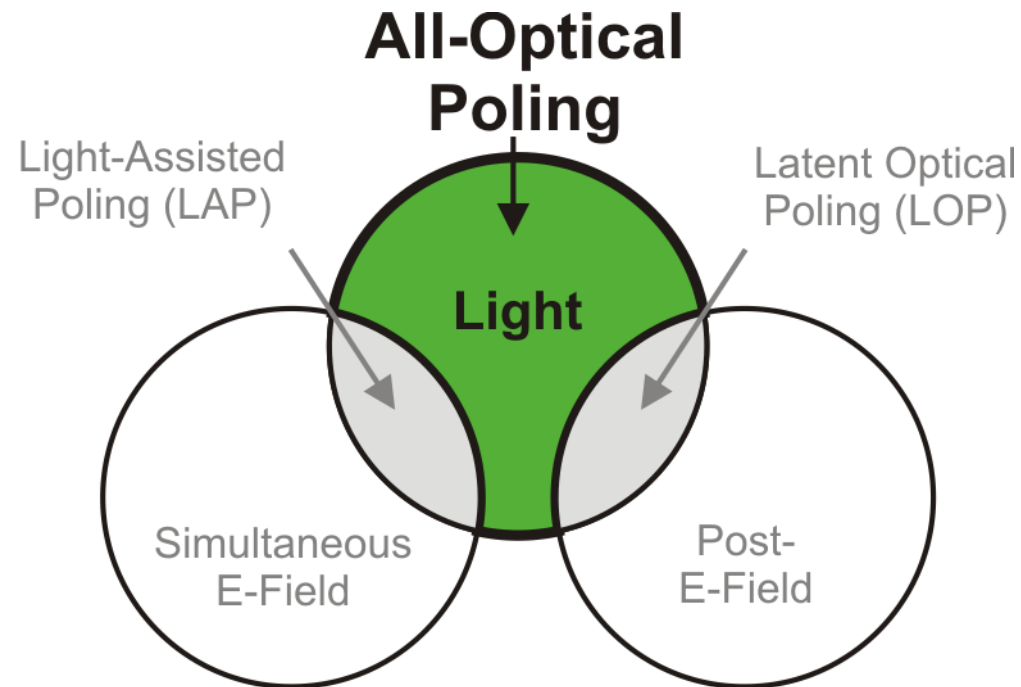
$\lambda = 514$ nm
c.w. light

3. Domain inversion (nucleation): fs

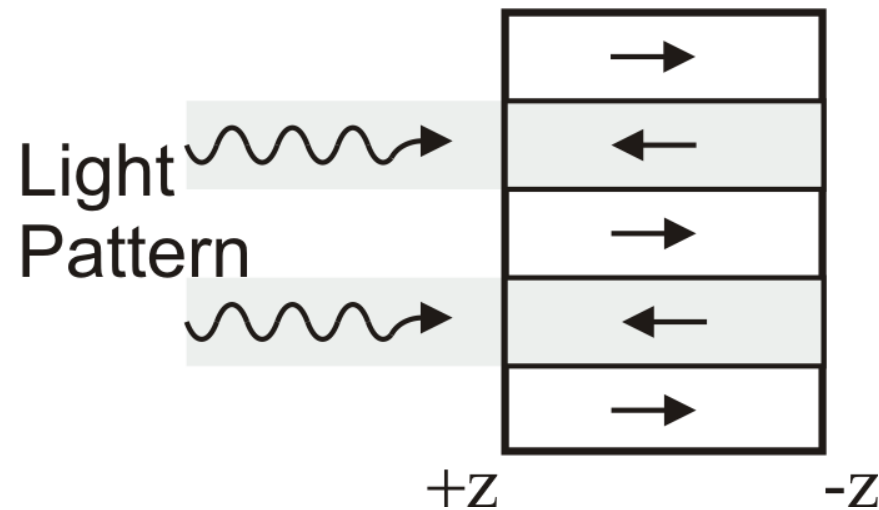
- Optically periodically poled lithium niobate (OPPLN)



4. All optical poling?

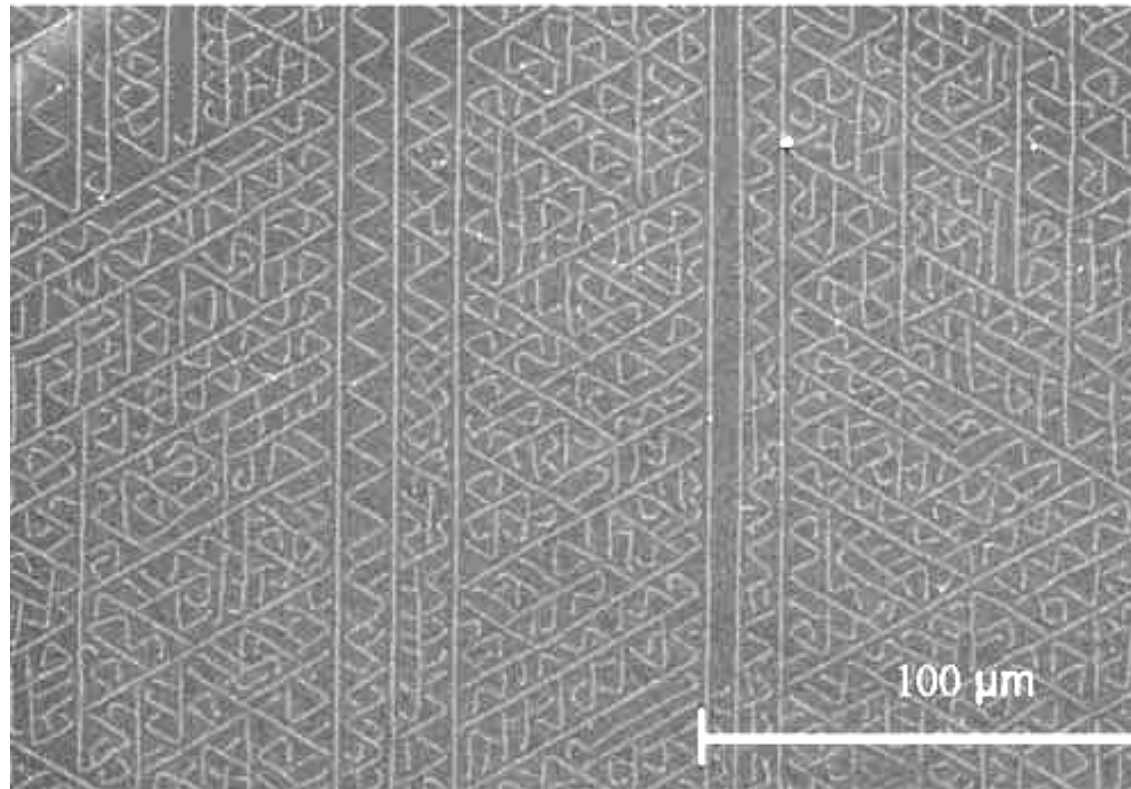


4. AOP



Use structured light to
control local poling

4. All optical poling: unstructured light

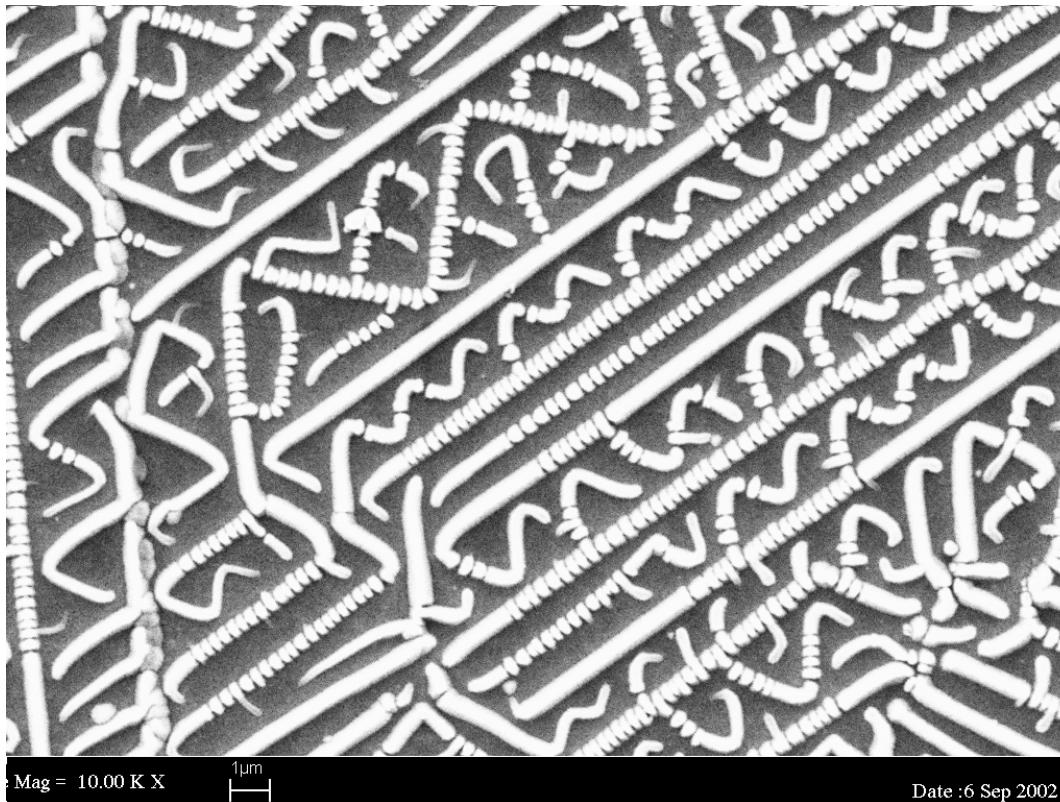


University
of Southampton

Pulsed UV light (CLF tunable dye laser) and 266nm



4. Unstructured light: Self-organisation:



Previous light induced optical patterns using c.w vis light plus HF acid bath

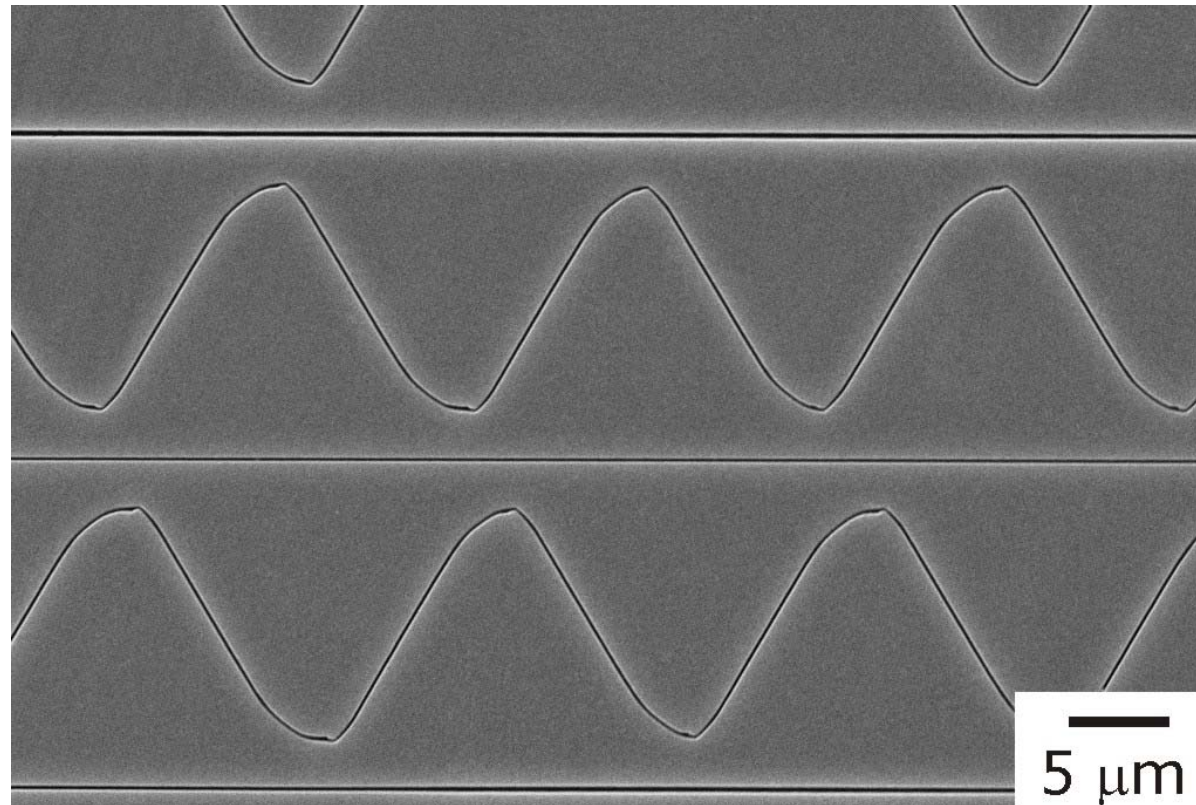


University
of Southampton

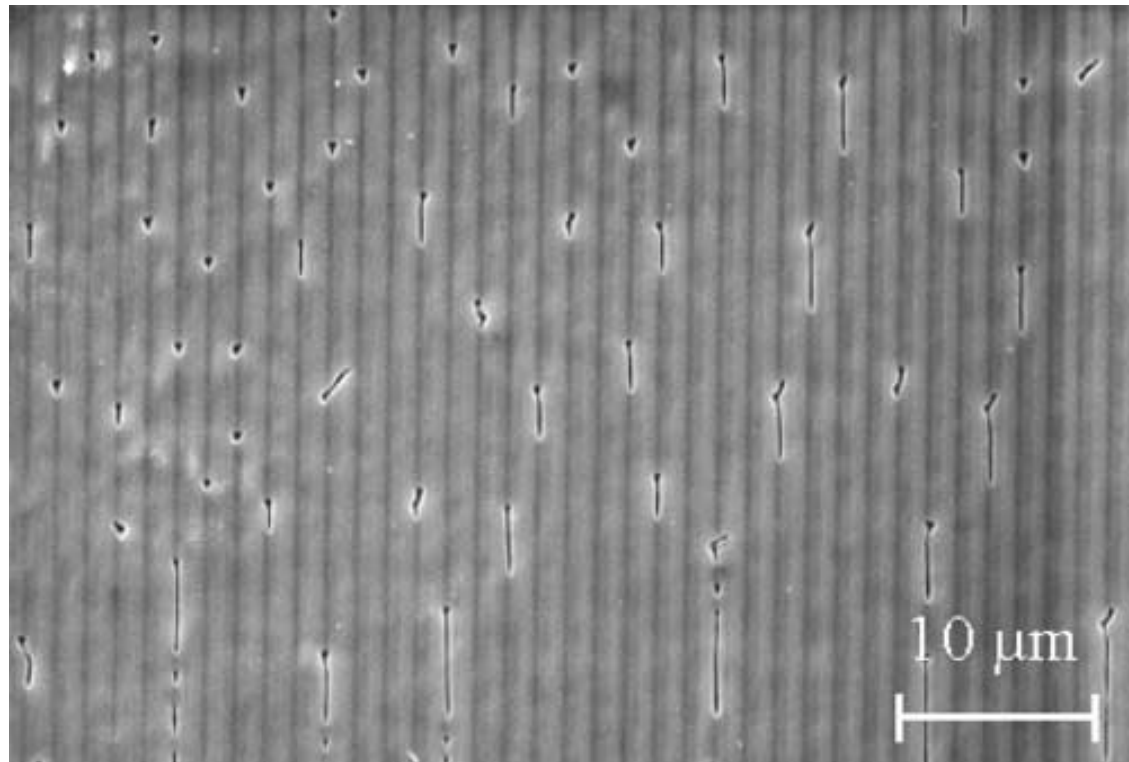
10µm



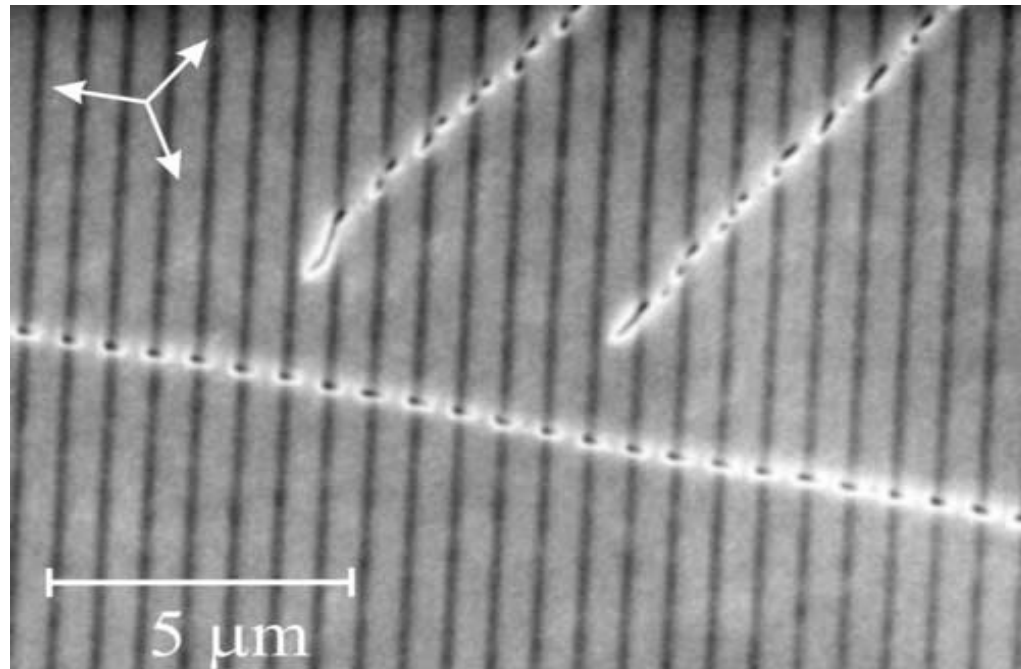
4. Unstructured light: Self-organisation:



4. All optical poling: structured light.

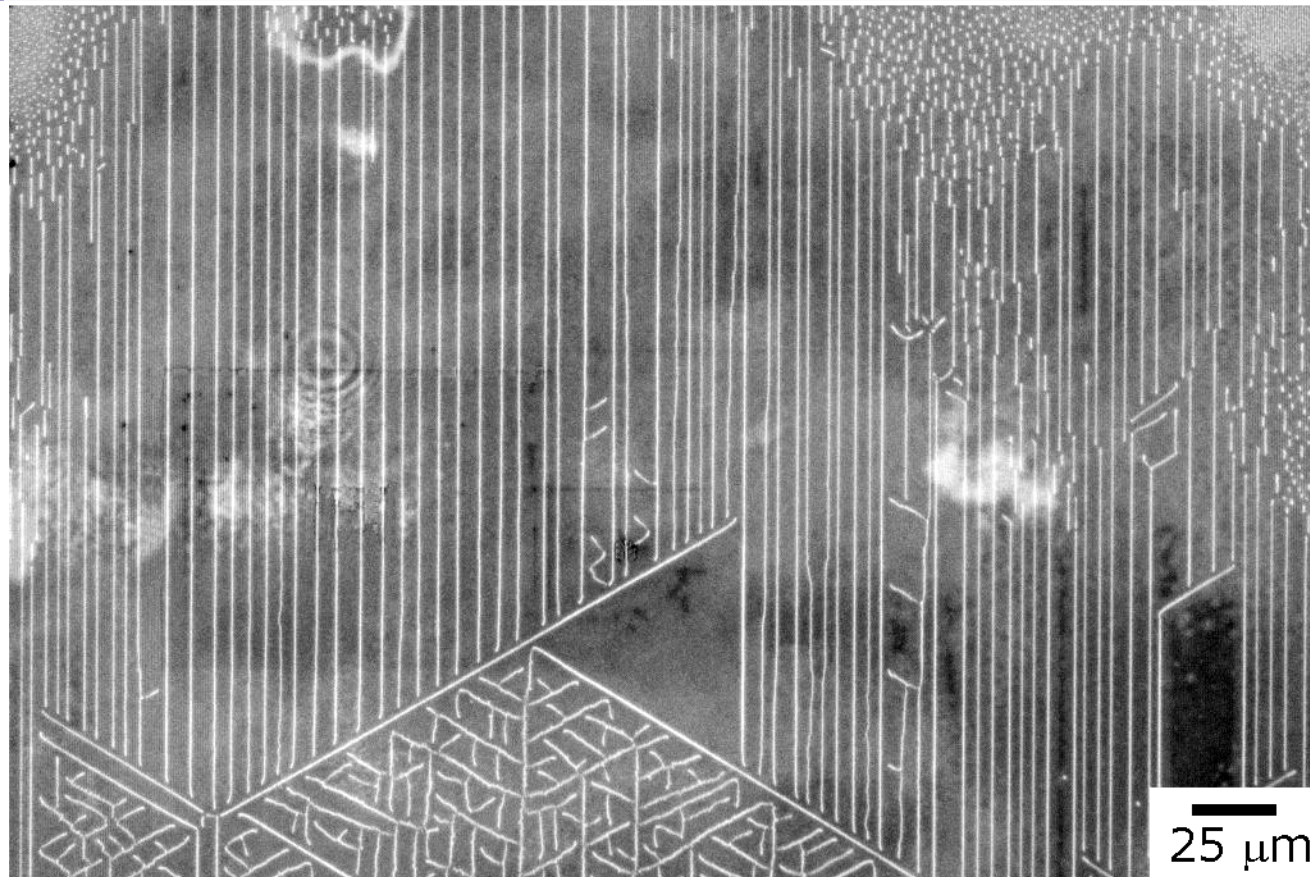


4. All optical poling: structured light.



Poling occurs only at local optical maxima.

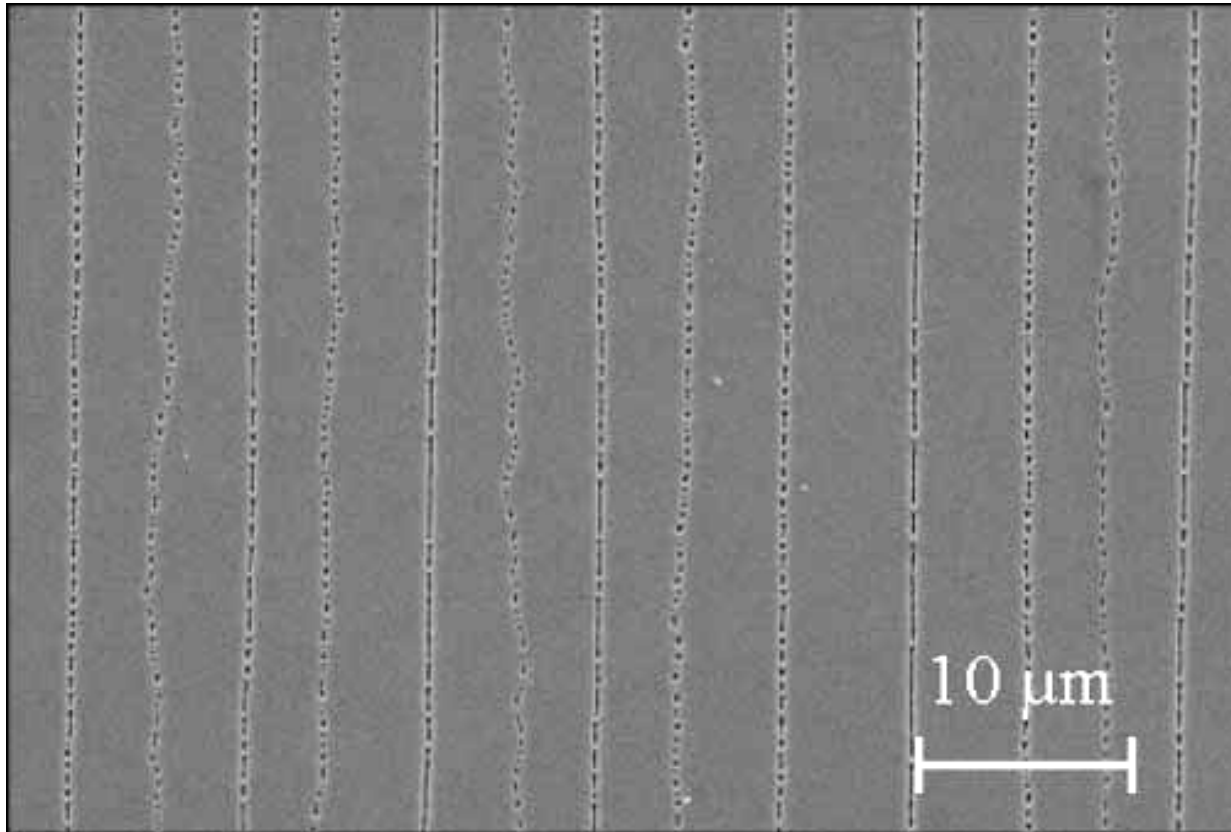
4. AOP: more uniform results.



University
of Southampton



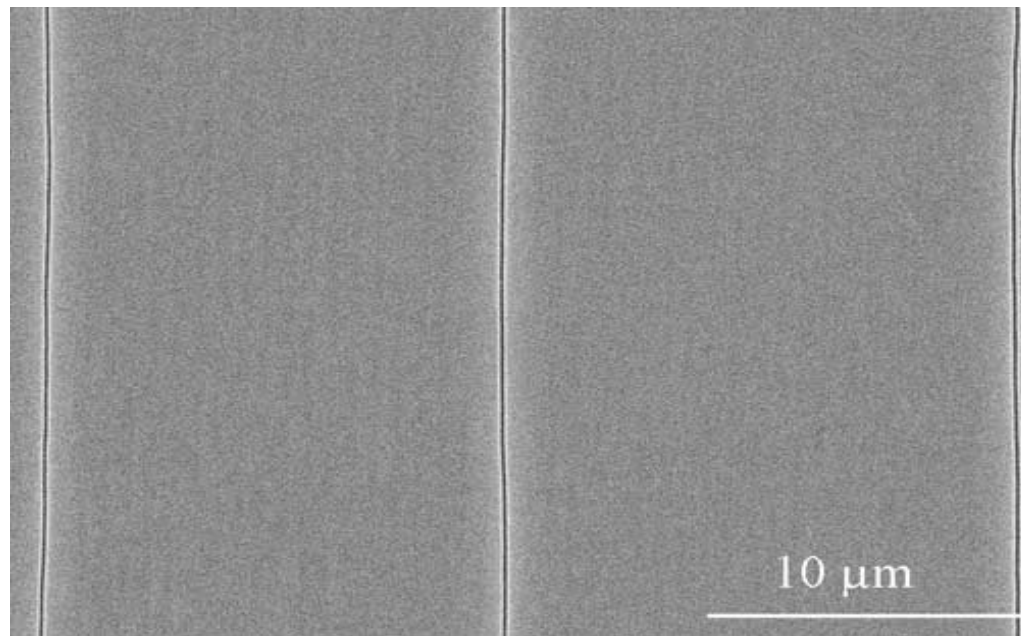
4. AOP: 'quasi-periodicity'



University
of Southampton

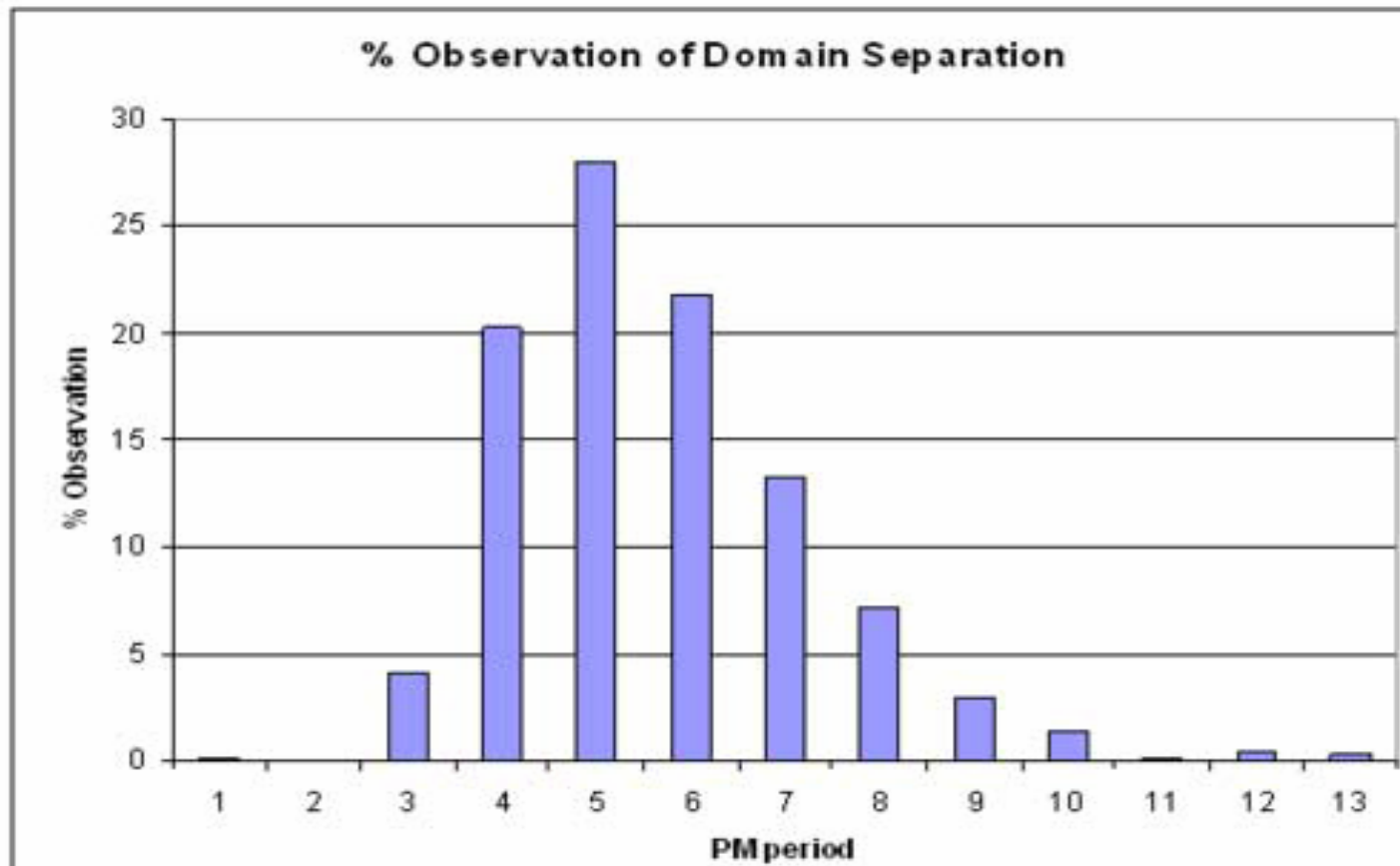


4. AOP at 150 degrees C

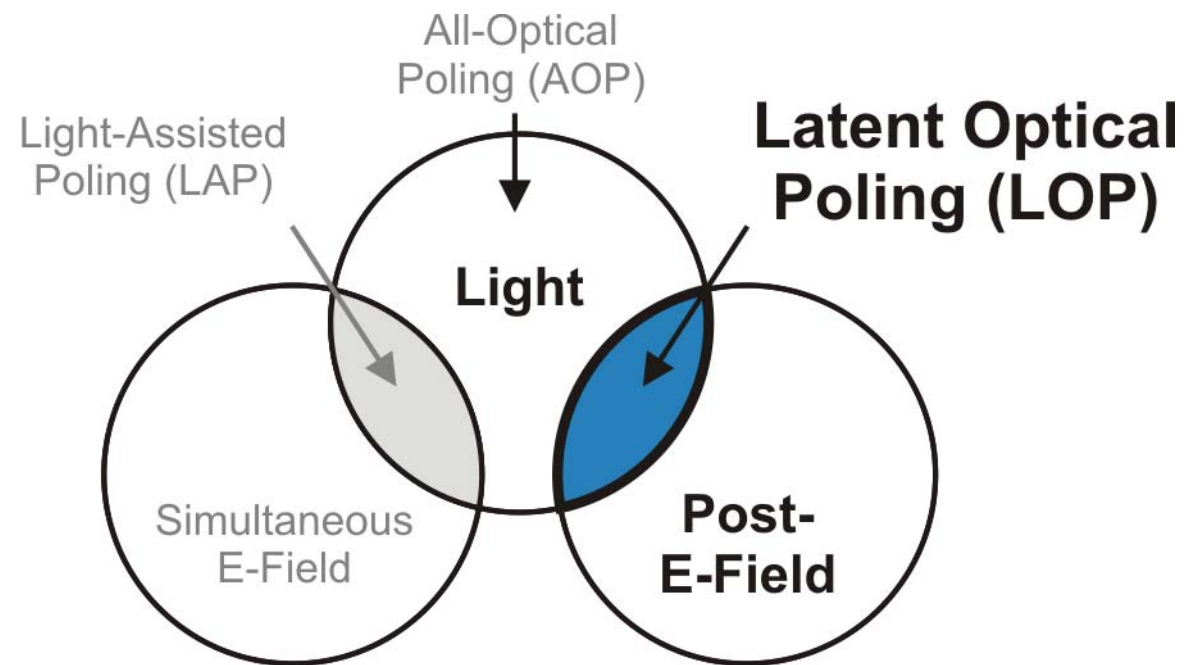


Continuous domain lines:
spacing of 15μm!

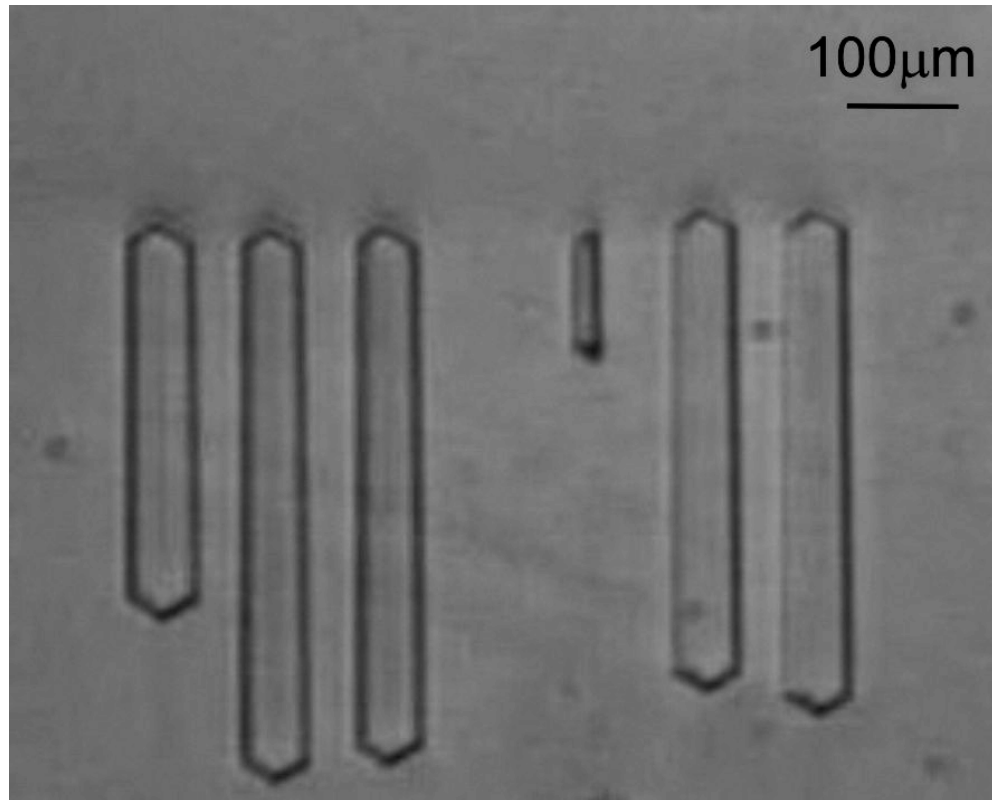
4. AOP periodicity data.



5. Latent optical poling (LOP)



5. Latent poling (FRED laser)



pre-illuminated lines
(0.5mm in lengths)
scanned (on the +z face)
with variable speeds
(12.5-50 μm/s) at an
incident intensity of ~275
kW/cm².

The image shows the
domains formed ~40
minutes after
illumination.

6. Mechanisms

Possible mechanisms:

- Ablation force (piezoelectric) → local E-field
- Local heating (pyroelectric) → local E-field
- Li out-diffusion (unlikely...)
- Photoconductivity modification (possible)

M. Wengler JAP 2005 ($\lambda = 304$ nm):

highly absorbed UV light modifies the E-field distribution due to non-uniform conductivity induced by photoconductivity

6. Mechanisms/conclusions

- **AOP** does not produce closely spaced domain features:
electrostatic repulsion in weakly interacting system.
- **LAP** does produce these features, and fs looks most promising.
scanned exposure produced good quality OPPLN
- **LOP** may be the best of all: = photographic printing.

Publications and acknowledgments

- Publications listed at
<http://www.orc.soton.ac.uk/intaltpub.html>
- Thanks to CLF staff:
 - Ian Clark in particular.